Quad Bus Buffer

with 3-State Control Inputs

The MC74VHCT126A is a high speed CMOS quad bus buffer fabricated with silicon gate CMOS technology. It achieves noninverting high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74VHCT126A requires the 3-state control input (OE) to be set Low to place the output into high impedance.

The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3 V to 5.0 V, because it has full 5.0 V CMOS level output swings.

The VHCT126A input structures provide protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. The output structures also provide protection when V_{CC} = 0 V. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

- High Speed: $t_{PD} = 3.8 \text{ ns}$ (Typ) at $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4.0 \mu A$ (Max) at $T_A = 25^{\circ}C$
- TTL-Compatible Inputs: $V_{IL} = 0.8 \text{ V}$; $V_{IH} = 2.0 \text{ V}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Low Noise: $V_{OLP} = 0.8 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 72 FETs or 18 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant



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MARKING DIAGRAMS



SOIC-14 D SUFFIX CASE 751A



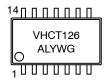


TSSOP-14 DT SUFFIX CASE 948G





SOEIAJ-14 M SUFFIX CASE 965



A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or ■ = Pb-Free Package

See Applications Note #AND8004/D for date code and traceability information.

FUNCTION TABLE

VHCT126A				
Ir	puts	Outputs		
Α	OE	Υ		
Н	Н	Н		
L	Н	L		
X	L	Z		

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

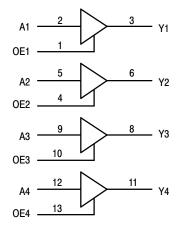


Figure 1. LOGIC DIAGRAM Active-High Output Enables

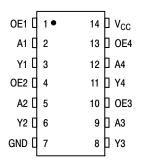


Figure 2. PIN ASSIGNMENT

MAXIMUM RATINGS

Rating	Rating			Unit
DC Supply Voltage		V _{CC}	- 0.5 to + 7.0	٧
DC Input Voltage		V _{in}	- 0.5 to + 7.0	٧
DC Output Voltage	Output in 3–State High or Low State	V _{out}	-0.5 to + 7.0 $-0.5 \text{ to } V_{CC} + 0.5$	V
Input Diode Current		I _{IK}	- 20	mA
Output Diode Current (V _{OUT} <	GND; V _{OUT} > V _{CC})	lok	± 20	mA
DC Output Current, per Pin		l _{out}	± 25	mA
DC Supply Current, V _{CC} and C	GND Pins	I _{CC}	± 75	mA
Power Dissipation in Still Air,	SOIC Packages† TSSOP Package†	P _D	500 450	mW
Storage Temperature		T _{stg}	- 65 to + 150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — SOIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Parame	Symbol	Min	Max	Unit	
DC Supply Voltage		V _{CC}	4.5	5.5	V
DC Input Voltage		V _{in}	0	5.5	V
DC Output Voltage	Output in 3–State High or Low State	V _{out}	0 0	5.5 V _{CC}	V
Operating Temperature		T _A	- 40	+ 85	°C
Input Rise and Fall Time	$V_{CC} = 5.0 \text{ V } \pm 0.5 \text{ V}$	t _r , t _f	0	20	ns/V

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	T _A = 25°C		T _A ≤	85°C	T _A ≤ 1	125°C		
Parameter	Test Conditions	Symbol	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
Minimum High-Level Input Voltage		V _{IH}	3.0 4.5 5.5	1.2 2.0 2.0			1.2 2.0 2.0		1.2 2.0 2.0		V
Maximum Low-Level Input Voltage		V _{IL}	3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	V
Minimum High-Level Output Voltage V _{IN} = V _{IH} or V _{II}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu\text{A}$	V _{OH}	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		٧
AIN = AIH OI AIF	$\begin{aligned} V_{IN} &= V_{IH} \text{ or } V_{IL} \\ I_{OH} &= -4.0 \text{ mA} \\ I_{OH} &= -8.0 \text{ mA} \end{aligned}$		3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
Maximum Low-Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $I_{OL} = 50 \mu A$	V _{OL}	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	٧
$V_{IN} = V_{IH}$ or V_{IL}	$\begin{aligned} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OL} = 4.0 \text{ mA} \\ &I_{OL} = 8.0 \text{ mA} \end{aligned}$		3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	I _{IN}	0 to 5.5			± 0.1		±1.0		± 1.0	μА
Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND	I _{CC}	5.5			2.0		20		40	μΑ
Quiescent Supply Current	Input: V _{IN} = 3.4 V	I _{CCT}	5.5			1.35		1.50		1.65	mA
Maximum 3–State Leakage Current	$V_{IN} = V_{IH} \text{ or } V_{I}$ $V_{OUT} = V_{CC} \text{ or GND}$	l _{OZ}	5.5			±0.2 5		±2.5		±2.5	μΑ
Output Leakage Current	V _{OUT} = 5.5 V	I _{OPD}	0.0			0.5		5.0		10	μА

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

			T _A = 25°C		T _A = ≤	≤ 85°C	T _A ≤ 1	125°C		
Parameter	Test Conditions	Symbol	Min	Тур	Max	Min	Max	Min	Max	Unit
Maximum Propagation Delay, A to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$	t _{PLH} , t _{PHL}		5.6 8.1	8.0 11.5	1.0 1.0	9.5 13.0		12.0 16.0	ns
	$V_{CC} = 5.0 \pm 0.5 \text{ V} \begin{array}{c} C_L = 15 \text{ pF} \\ C_L = 50 \text{ pF} \end{array}$			3.8 5.3	5.5 7.5	1.0 1.0	6.5 8.5		8.5 10.5	
Maximum Output Enable TIme, OE to Y	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	t _{PZL} , t _{PZH}		5.4 7.9	8.0 11.5	1.0 1.0	9.5 13.0		11.5 15.0	ns
	$\begin{array}{cccccccccccccccccccccccccccccccccccc$			3.6 5.1	5.1 7.1	1.0 1.0	6.0 8.0		7.5 9.5	
Maximum Output Disable Time, OE to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 50 \text{ pF}$ $R_L = 1.0 \text{ k}\Omega$	t _{PLZ} , t _{PHZ}		9.5	13.2	1.0	15.0		18.0	ns
	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 50 \text{ pF}$ $R_L = 1.0 \text{ k}\Omega$			6.1	8.8	1.0	10.0		12.0	
Output-to-Output Skew	V _{CC} = 3.3 ± 0.3 V C _L = 50 pF (Note 1)	t _{OSLH} , t _{OSHL}			1.5		1.5		2.0	ns
	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 50 \text{ pF}$ (Note 1)				1.0		1.0		1.5	
Maximum Input Capacitance		C _{in}		4	10		10		10	pF
Maximum Three-State Output Capacitance (Output in High Impedance State)		C _{out}		6						pF
	1		Typical @ 25°C, V _{CC} = 5.0V							
Power Dissipation Capacitance (Note 2)	C _{PD}				15				pF

Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|.
 C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/4 (per buffer). C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$, $C_L = 50 \text{pF}$, $V_{CC} = 5.0 \text{V}$)

		T _A = 25°C		
Characteristic	Symbol	Тур	Max	Unit
Quiet Output Maximum Dynamic V _{OL}	V _{OLP}	0.3	0.8	V
Quiet Output Minimum Dynamic V _{OL}	V _{OLV}	- 0.3	- 0.8	V
Minimum High Level Dynamic Input Voltage	V_{IHD}		3.5	٧
Maximum Low Level Dynamic Input Voltage	V_{ILD}		1.5	V

SWITCHING WAVEFORMS

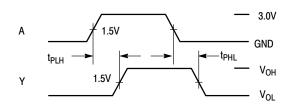


Figure 3.

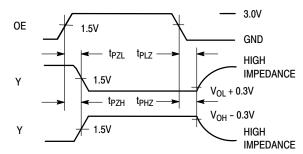
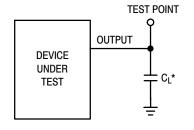


Figure 4.



^{*}Includes all probe and jig capacitance

DEVICE UNDER TEST C_L^* TEST POINT

OUTPUT $1 \text{ k}\Omega$ OUTPUT $1 \text{ k}\Omega$ CONNECT TO V_{CC} WHEN TESTING t_{PLZ} AND t_{PZL} .

CONNECT TO GND WHEN TESTING t_{PHZ} AND t_{PZH} .

Figure 5. Test Circuit Figure 6. Test Circuit

ORDERING INFORMATION

Device	Package	Shipping [†]
M74VHCT126ADTR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74VHCT126AMG	SOEIAJ-14 (Pb-Free)	50 Units / Rail
MC74VHCT126AMELG	SOEIAJ-14 (Pb-Free)	2000 / Tape & Reel
MC74VHCT126ADTRG	TSSOP-14* (Pb-Free)	2500 Tape & Reel

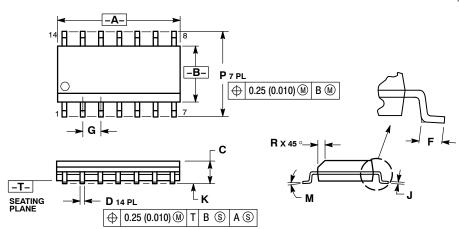
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}Includes all probe and jig capacitance

^{*}This package is inherently Pb-Free.

PACKAGE DIMENSIONS

SOIC-14 **D SUFFIX** CASE 751A-03 **ISSUE J**



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

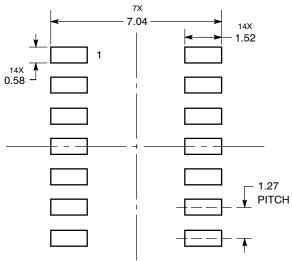
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 5. DIMENSION D DOES NOT INCLUDE.
- PEH SIDE.
 5. DIMENSION D DOES NOT INCLUDE
 DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.127
 (0.005) TOTAL IN EXCESS OF THE D
 DIMENSION AT MAXIMUM MATERIAL
 CONDITION.

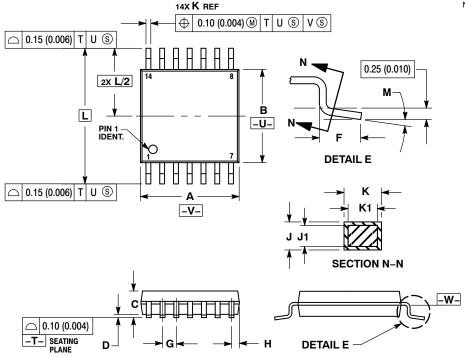
	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
Κ	0.10	0.25	0.004	0.009
М	0 °	7°	0 °	7 °
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

SOLDERING FOOTPRINT



PACKAGE DIMENSIONS

TSSOP-14 **DT SUFFIX** CASE 948G-01 **ISSUE B**



NOTES:

- DTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

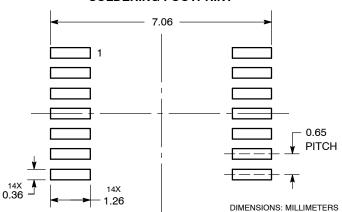
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL (U.U.S) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

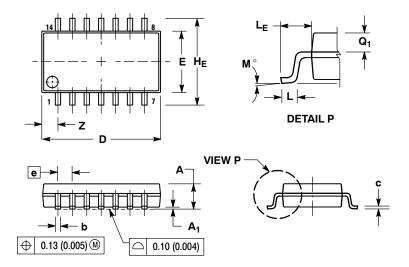
	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
C		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
Κ	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40		0.252	BSC
М	0°	8 °	0 °	8 °

SOLDERING FOOTPRINT



PACKAGE DIMENSIONS

SOEIAJ-14 **M SUFFIX** CASE 965-01 **ISSUE B**



- DIMENSIONING AND TOLERANCING PER ANSI 1. DIMENSIO Y14.5M, 1982
- CONTROLLING DIMENSION: MILLIMETER.
- MOLD FLASH OR PROTRUSION. MILEMELET.

 MOLD FLASH OR PROTRUSIONS AND ARE
 MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION, ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.

 DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.10	0.20	0.004	0.008
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27	1.27 BSC		BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q_1	0.70	0.90	0.028	0.035
Z		1.42		0.056

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